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Quarterly Reliability Monitoring Results

Quarters: Q1/2022 to Q4/2023 Based on structural similarity

Supplier		User Part Number						
Nexperia B.V.		BAS16QA-Q						
Name of Laboratory		Part Description						
Assembly reliability labs Based on AEC-Q101 Test		Nexperia DHAM	Small Signal I	Bipolar Diode				
		MCD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
24004 0117	TEST		2 di di oli		<i>"</i> qu untty	"		
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113	,,,		un purco	500 50.011		
		Bake Tamb = $125 ^{\circ}\text{C}$	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	212	9600	0		
		MIL-STD-750-1	,	-14	2000			
	HTRB	MIL-STD-750-1 M1038 Method A						
		$T_j = T_j max$, $Vr = 100\%$ of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	110	4920	0		
# DI	Dias	Teverse voltage	1000 110015	110	4920	0		
	тс	150022 4104						
# A4	Temperature Cycling	JESD22-A104 -65 °C to Timax, not to exceed 150°C	1000	52	2400	0		
# A4	Temperature Cycling	-65 °C to Tjillax, not to exceed 150°C	1000 cycles	53	2400	0		
		150522 4440						
# 42 ==	UHAST Unbiased HAST	JESD22-A118						
# A3 or	UTDIased HAST	Tamb = 130 °C, RH = 85 %	- 96 hours	53	2400	0		
		JESD22-A102						
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)						
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias	rated reverse voltage ^[1]	1000 hours	53	2400	0		
		MIL-STD-750 Method 1037						
	IOL	ton = toff, devices powered to insure ΔTj =						
# A5	Intermittent Operating Life	100 °C for 15000 cycles	1000 hours	53	2400	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	n.a.	n.a.	n.a.		
	SD							
# C10	Solderability	J-STD-002		37	1110	0		

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab T	Fechnology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia					
DHAM S	Small Signal Bipolar Diode	4920	0	0,86	1,16E+09

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